

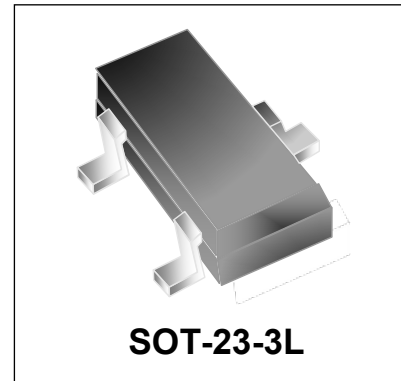
N-Channel Enhancement MOSFET

Features

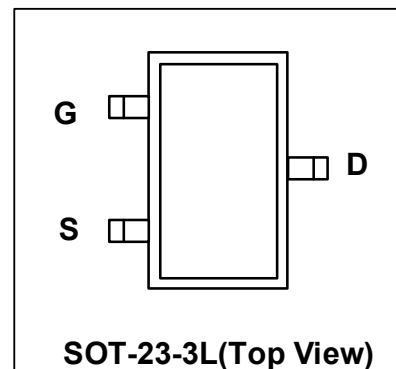
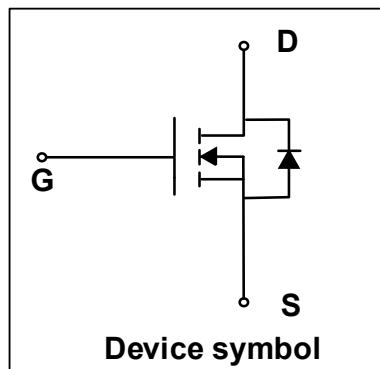
- Way-on Small Signal MOSFETs
- $V_{DS} = 100V$, $I_D = 3.5A$
 $R_{DS(on)} < 90m\Omega @ V_{GS} = 10V$
 $R_{DS(on)} < 110m\Omega @ V_{GS} = 4.5V$
- Low Gate Charge
- Trench LV MOSFET Technology

Mechanical Characteristics

- SOT-23-3L Package
- Marking : Making Code
- RoHS Compliant



Schematic & PIN Configuration



Absolute Maximum Rating ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	3.5	A
Pulsed Drain Current ¹	I_{DM}	14	A
Power Dissipation	P_D	1.65	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^{\circ}C$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Ambient ²	$R_{\theta JA}$	76	$^{\circ}C/W$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250μA	100	-	-	V
Gate Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	-	-	±100	nA
Drain Cut-off Current	I _{DSS}	V _{DS} = 100V, V _{GS} = 0V	-	-	1	μA
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D = 250μA	1.4	-	2.4	V
Drain-Source on-state Resistance ³	R _{DS(on)}	V _{GS} = 10V, I _D = 2A	-	74	90	mΩ
		V _{GS} = 4.5V, I _D = 1A	-	87	110	
Dynamic Characteristics⁴						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 50V, f = 1MHz	-	1150	-	pF
Output Capacitance	C _{oss}		-	32	-	
Reverse Transfer Capacitance	C _{rss}		-	26	-	
Switching Characteristics⁴						
Total gate charge	Q _g	V _{GS} = 10V, V _{DS} = 50V, I _D = 2A	-	21	-	nC
Gate-source charge	Q _{gs}		-	3.7	-	
Gate-drain charge	Q _{gd}		-	3.6	-	
Turn-on Time	t _{d(on)}	V _{GS} = 10V, V _{DD} = 50V, R _G = 3Ω, I _D = 2A	-	5.8	-	ns
Rise time	t _r		-	16	-	
Turn-off Time	t _{d(off)}		-	18.5	-	
Fall time	t _f		-	7.2	-	
Source-Drain Diode characteristics						
Body Diode Voltage ³	V _{SD}	I _S = 1A, V _{GS} = 0V	-	-	1.2	V
Continuous Source Current	I _S	-	-	-	3.5	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C.
2. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width≤300μs, duty cycle≤2%.
4. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

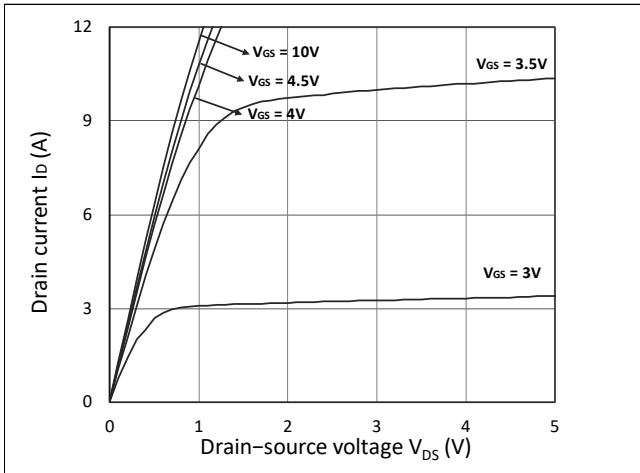


Figure 1. Output Characteristics

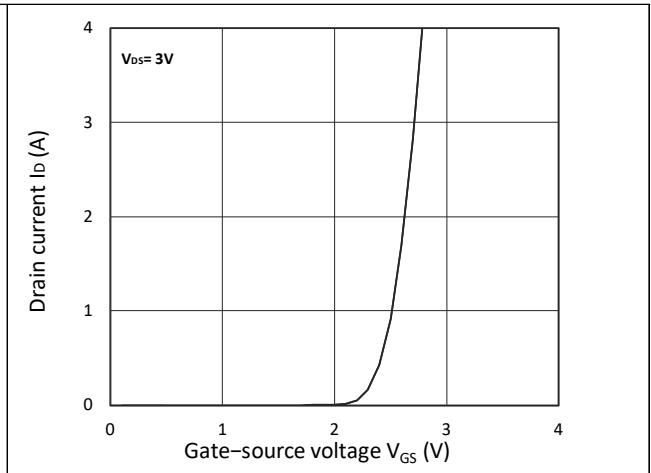


Figure 2. Transfer Characteristics

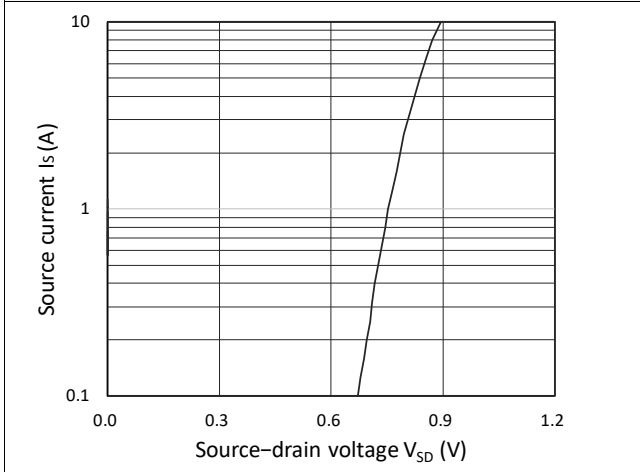


Figure 3. Forward Characteristics of Reverse

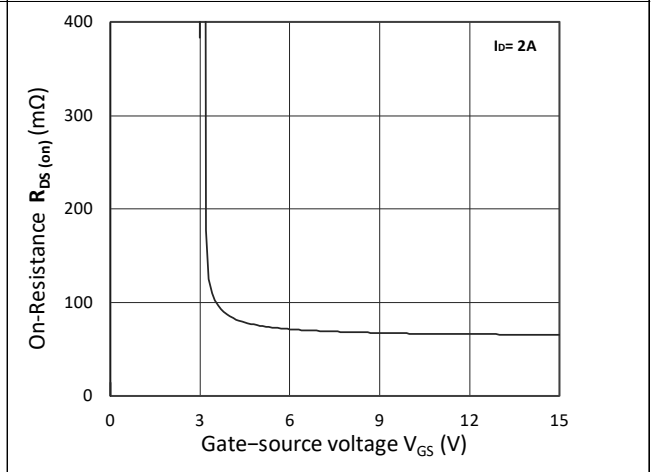


Figure 4. $R_{DS(on)}$ vs. V_{GS}

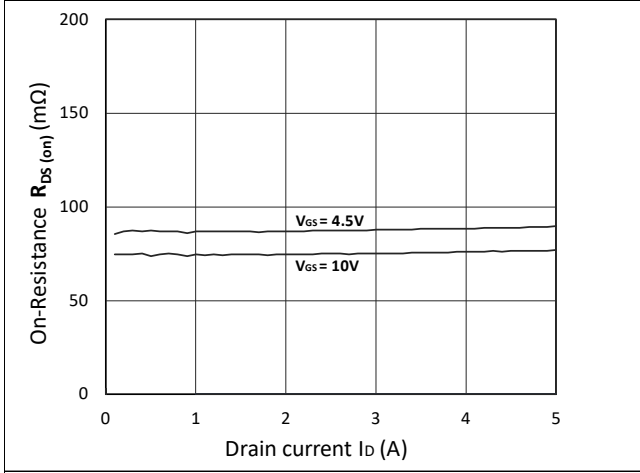


Figure 5. $R_{DS(on)}$ vs. I_D

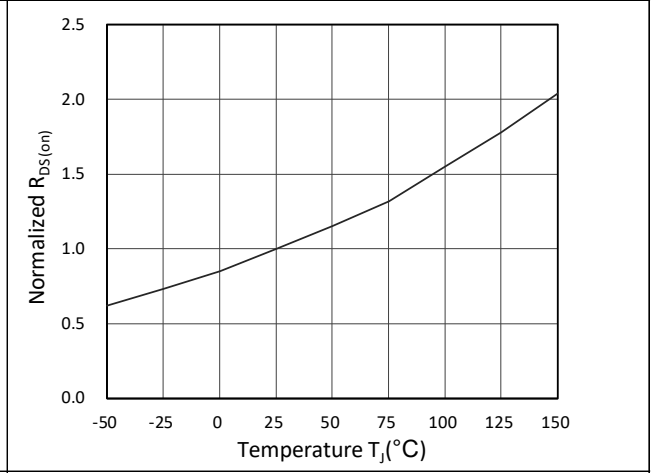


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

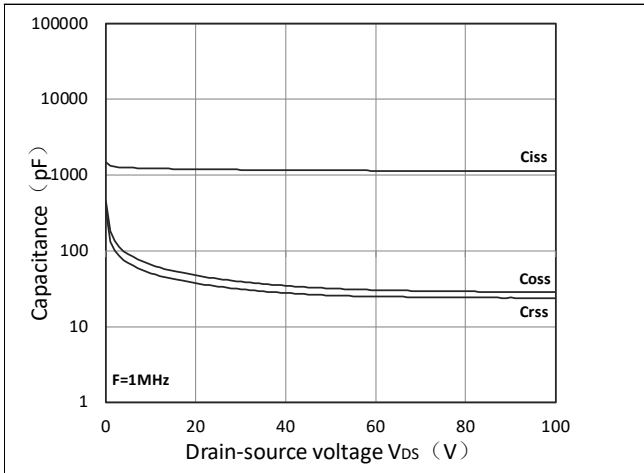


Figure 7. Capacitance Characteristics

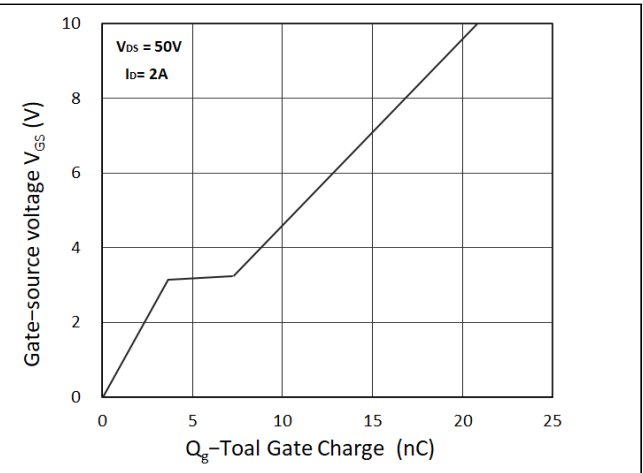
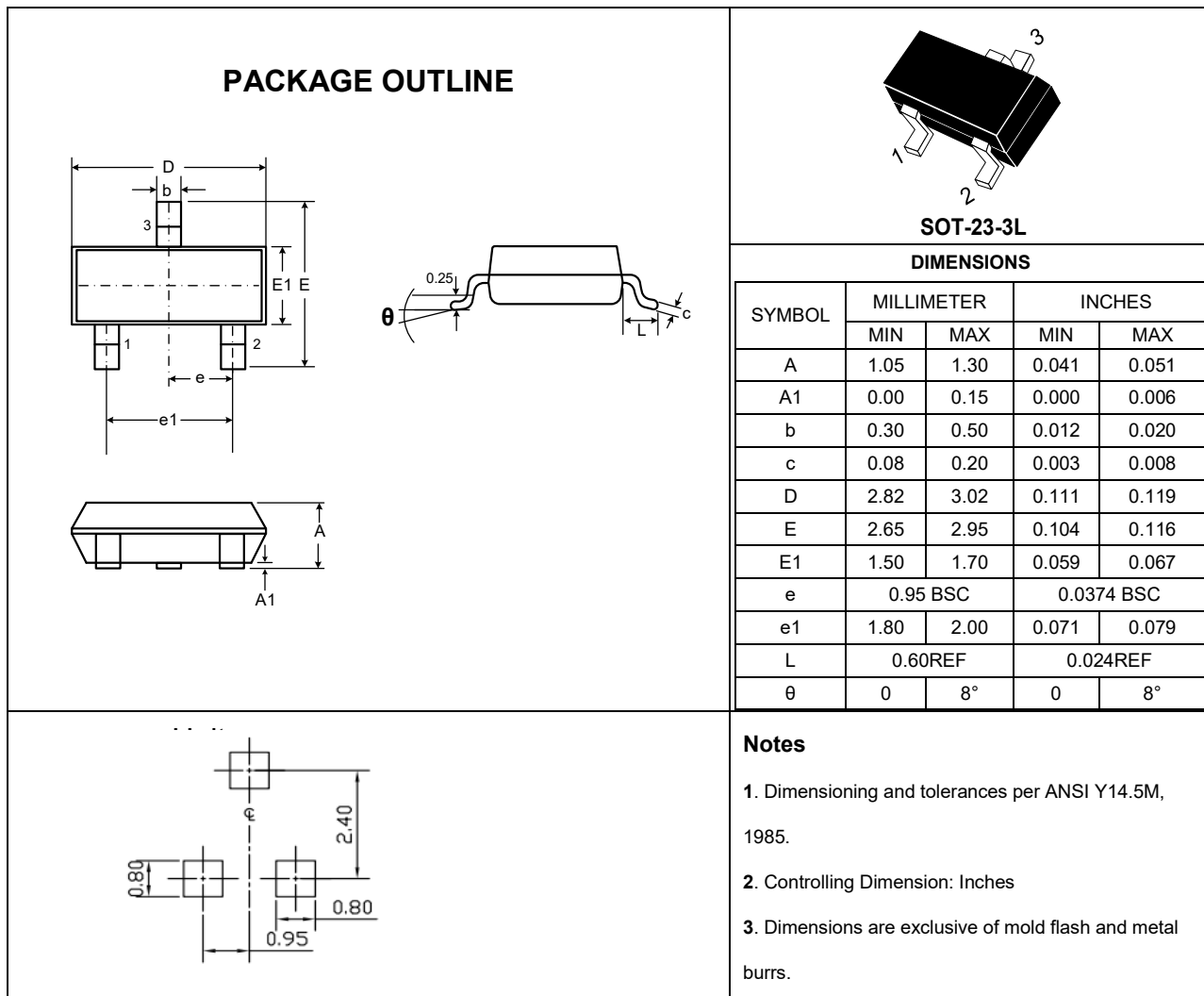


Figure 8. Gate Charge Characteristics

Outline Drawing – SOT-23-3L



Marking Codes

Part Number	WM10N35M2
Marking Code	

Package Information

Qty: 3k/Reel

CONTACT INFORMATION

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For additional information, please contact your local Sales Representative.

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Specifications are subject to change without notice.
The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.
Users should verify actual device performance in their specific applications.